

DMP21D0UFB

20V P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

$V_{(BR)DSS}$	$R_{DS(on) Max}$	$I_D Max$ @ $T_A = 25^\circ C$ (Note 4)
-20V	495m Ω @ $V_{GS} = -4.5V$	-0.77A
	690m Ω @ $V_{GS} = -2.5V$	-0.67A
	960m Ω @ $V_{GS} = -1.8V$	-0.57A

Description and Applications

This MOSFET has been designed to minimize the on-state resistance ($R_{DS(on)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Portable electronics

Features and Benefits

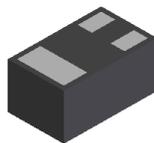
- Footprint of just 0.6mm² – thirteen times smaller than SOT23
- Low Gate Threshold Voltage
- Fast Switching Speed
- **Totally Lead-Free & Fully RoHS compliant (Note 1)**
- **Halogen and Antimony Free. "Green" Device (Note 2)**
- **ESD Protected Gate 3KV**
- **Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

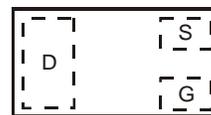
- Case: X1-DFN1006-3
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – NiPdAu over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.001 grams (approximate)



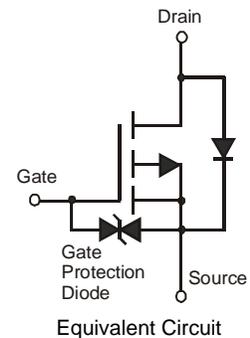
X1-DFN1006-3



Bottom View



Top View
Internal Schematic



Ordering Information (Note 3)

Part Number	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
DMP21D0UFB-7B	NG	7	8	10,000

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. Halogen and Antimony free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 3. For packaging details, go to our website at <http://www.diodes.com>.

Marking Information

DMP21D0UFB-7B



Top View
Bar Denotes Gate
and Source Side

NG = Product Type Marking Code

Maximum Ratings @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	-20	V
Gate-Source Voltage			V_{GSS}	± 8	V
Continuous Drain Current	Steady State	$T_A = 25^\circ\text{C}$ (Note 4)	I_D	-0.77	A
		$T_A = 85^\circ\text{C}$ (Note 4)		-0.55	
		$T_A = 25^\circ\text{C}$ (Note 5)		-1.17	
Pulsed Drain Current (Note 6)			I_{DM}	-5.0	A

Thermal Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 4)	P_D	0.43	W
Power Dissipation (Note 5)	P_D	0.99	W
Thermal Resistance, Junction to Ambient (Note 4)	$R_{\theta JA}$	293	$^\circ\text{C/W}$
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	126	$^\circ\text{C/W}$
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

Thermal Characteristics

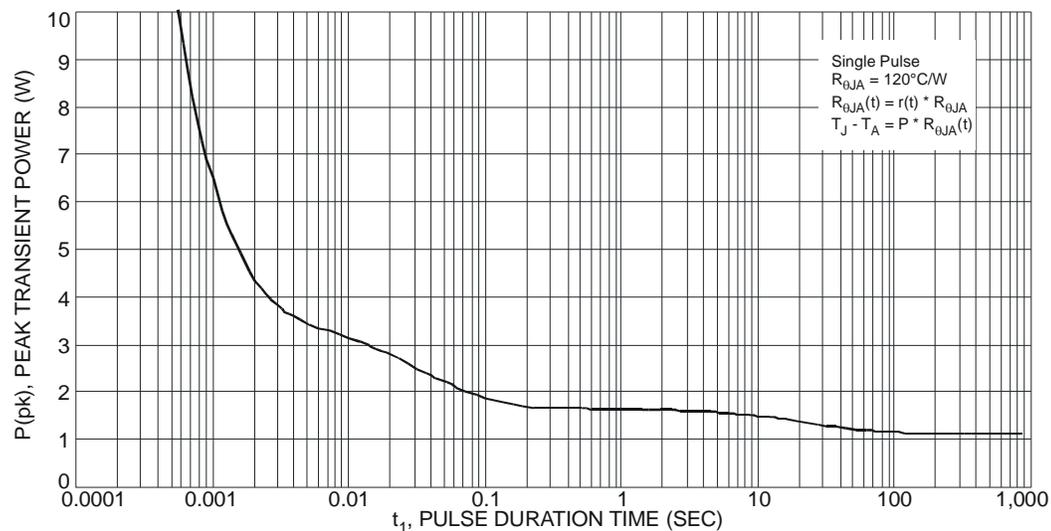


Fig. 1 Single Pulse Maximum Power Dissipation

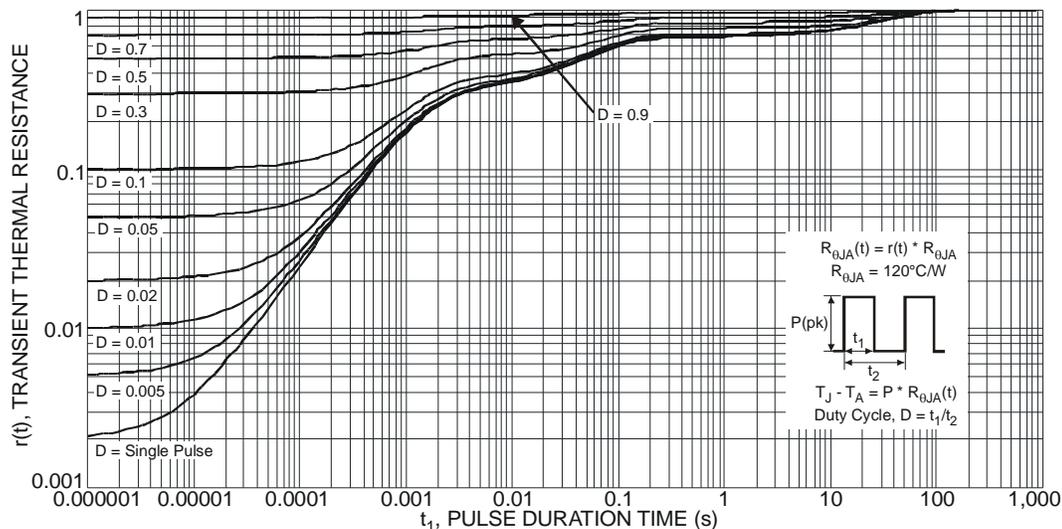


Fig. 2 Transient Thermal Response

Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	20	-	-	V	V _{GS} = 0V, I _D = -250μA
Zero Gate Voltage Drain Current T _J = 25°C	I _{DSS}	-	-	-1	μA	V _{DS} = -20V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	-	-	±10	μA	V _{GS} = ±8V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(th)}	-	-0.7	-	V	V _{DS} = V _{GS} , I _D = -250μA
Static Drain-Source On-Resistance	R _{DS(on)}	-	-	495	mΩ	V _{GS} = -4.5V, I _D = -400mA
				690		V _{GS} = -2.5V, I _D = -300mA
				960		V _{GS} = -1.8V, I _D = -100mA
Forward Transfer Admittance	Y _{fs}	50	-	-	mS	V _{DS} = -3V, I _D = -300mA
Diode Forward Voltage	V _{SD}	-	-	-1.2	V	V _{GS} = 0V, I _S = -300mA
DYNAMIC CHARACTERISTICS						
Input Capacitance	C _{iSS}	-	76.5	-	pF	V _{DS} = -10V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{oSS}	-	13.7	-	pF	
Reverse Transfer Capacitance	C _{rSS}	-	10.7	-	pF	
Gate Resistance	R _g	-	195	-	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge	Q _g	-	1.5	-	nC	V _{GS} = -8V, V _{DS} = -15V, I _D = -1A
Total Gate Charge	Q _g	-	1.0	-	nC	V _{GS} = -4.5V, V _{DS} = -15V, I _D = -1A
Gate-Source Charge	Q _{gs}	-	0.2	-	nC	
Gate-Drain Charge	Q _{gd}	-	0.3	-	nC	
Turn-On Delay Time	t _{D(on)}	-	7.1	-	ns	V _{DS} = -10V, -I _D = 1A V _{GS} = -4.5V, R _G = 6Ω
Turn-On Rise Time	t _r	-	8.0	-	ns	
Turn-Off Delay Time	t _{D(off)}	-	31.7	-	ns	
Turn-Off Fall Time	t _f	-	18.5	-	ns	

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout
 - Device mounted on FR-4 substrate PC board, 2oz copper, with thermal vias to bottom layer 1inch square copper plate
 - Device mounted on minimum recommended pad layout test board, 10% pulse duty cycle = 1%.
 - Short duration pulse test used to minimize self-heating effect.

Typical Characteristics

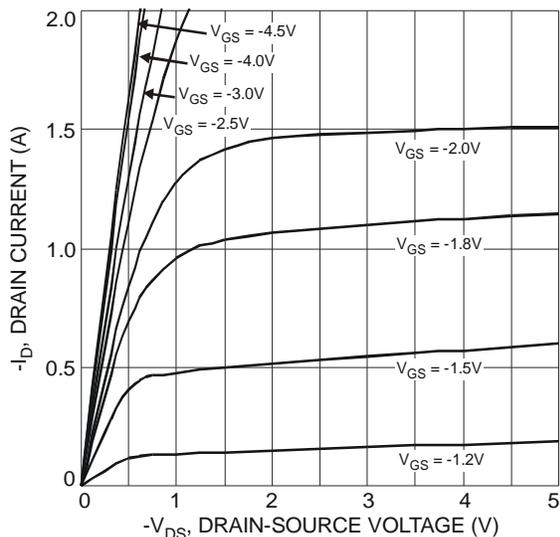


Fig. 3 Typical Output Characteristic

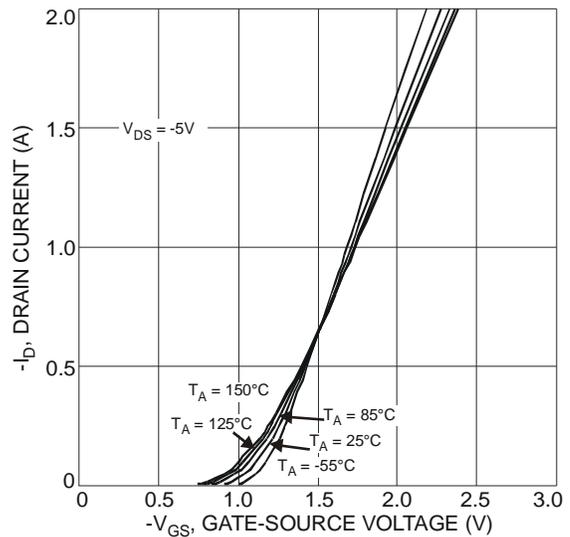


Fig. 4 Typical Transfer Characteristic

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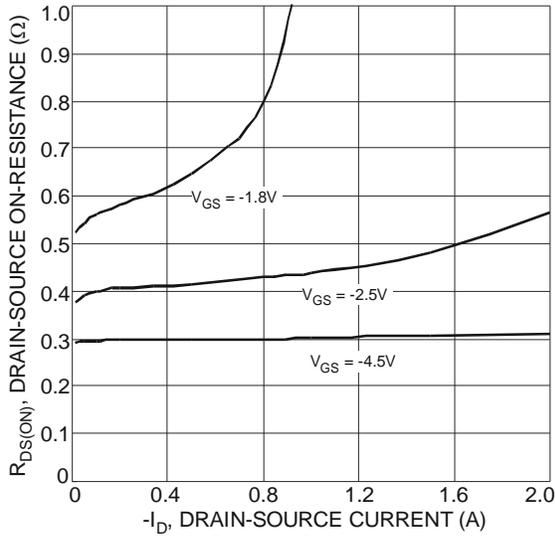


Fig. 5 Typical On-Resistance vs. Drain Current and Gate Voltage

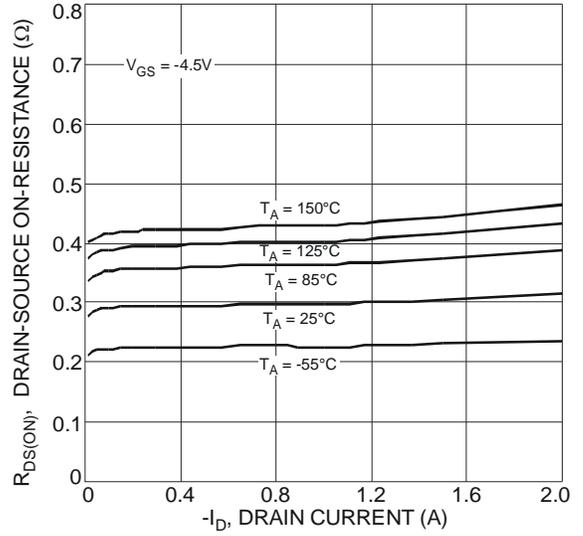


Fig. 6 Typical On-Resistance vs. Drain Current and Temperature

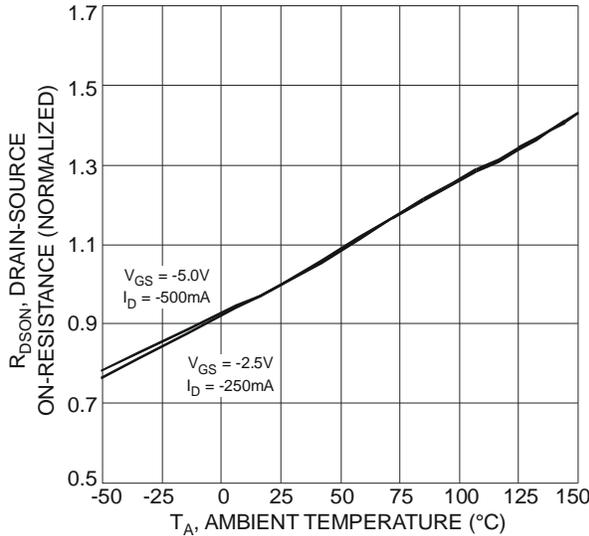


Fig. 7 On-Resistance Variation with Temperature

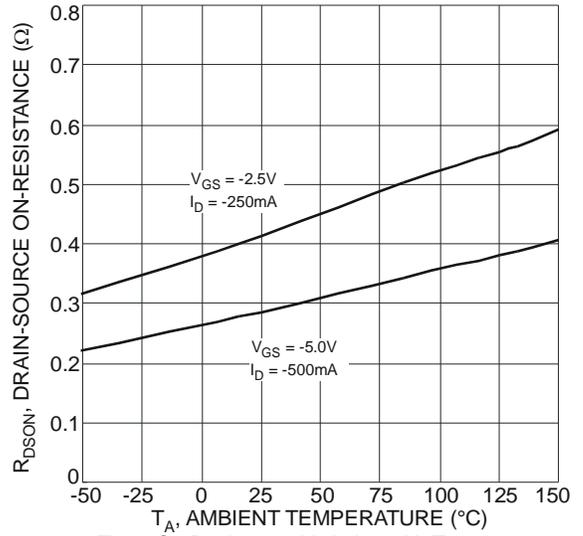


Fig. 8 On-Resistance Variation with Temperature

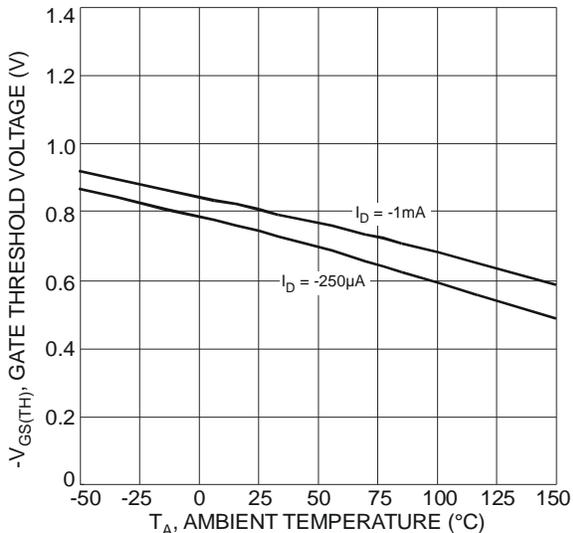


Fig. 9 Gate Threshold Variation vs. Ambient Temperature

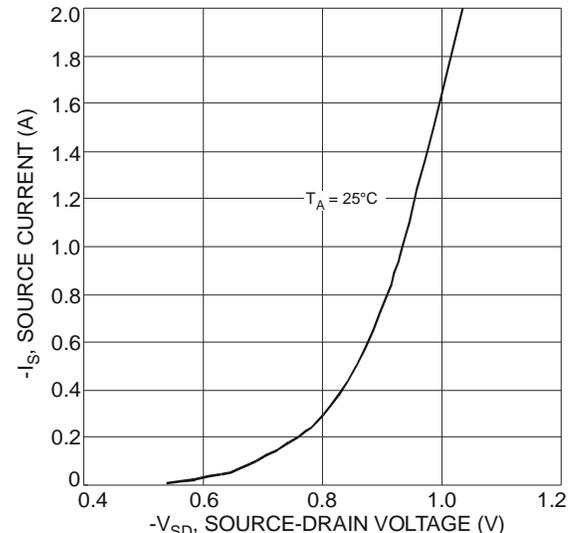


Fig. 10 Diode Forward Voltage vs. Current

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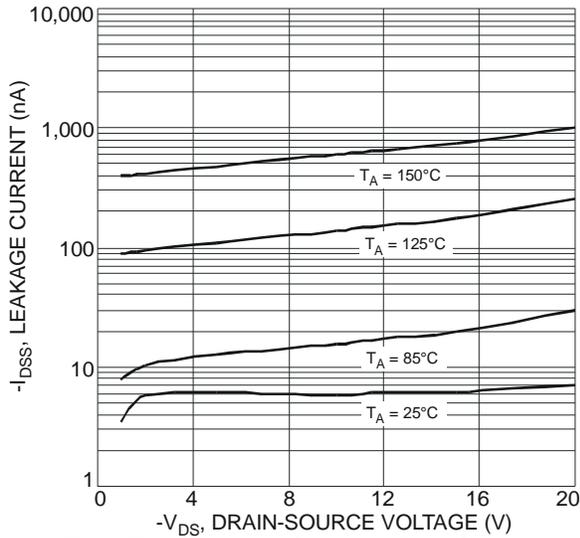


Fig. 11 Typical Leakage Current vs. Drain-Source Voltage

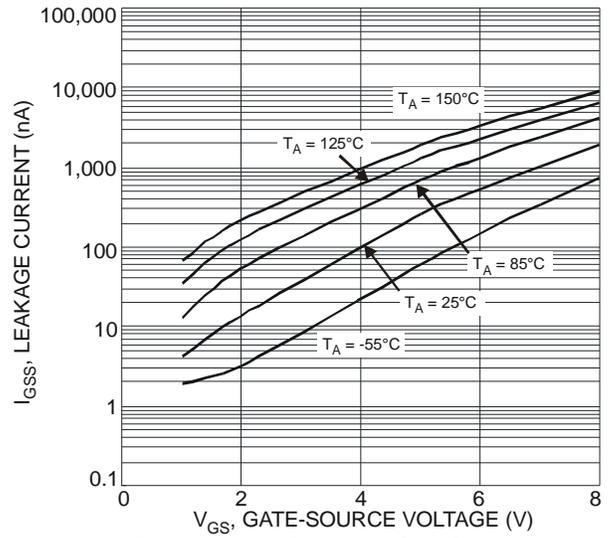


Fig. 12 Leakage Current vs. Gate-Source Voltage

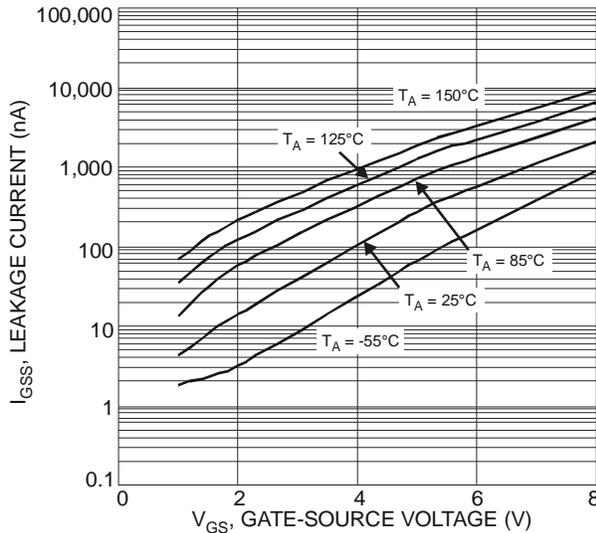


Fig. 13 Leakage Current vs. Gate-Source Voltage

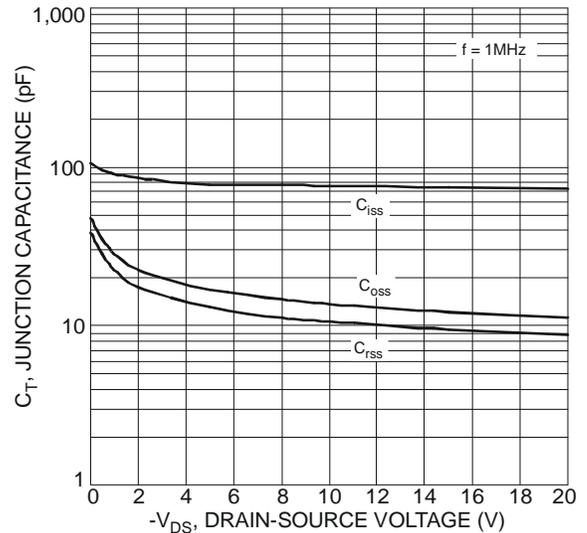


Fig. 14 Typical Junction Capacitance

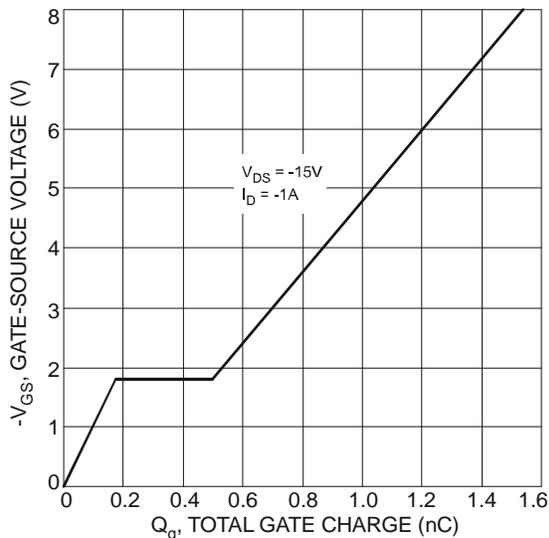
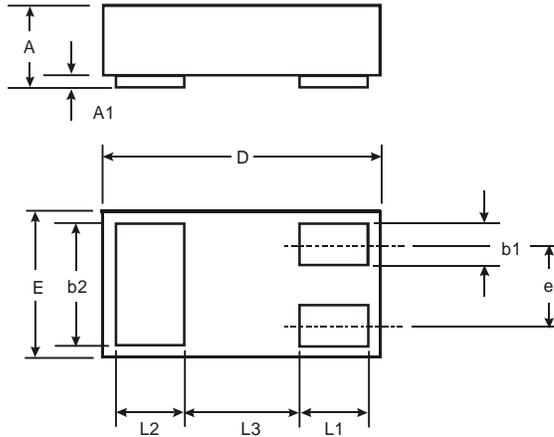


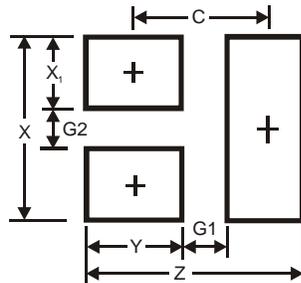
Fig. 15 Gate-Charge Characteristics

Package Outline Dimensions



X1-DFN1006-3			
Dim	Min	Max	Typ
A	0.47	0.53	0.50
A1	0	0.05	0.03
b1	0.10	0.20	0.15
b2	0.45	0.55	0.50
D	0.95	1.075	1.00
E	0.55	0.675	0.60
e	—	—	0.35
L1	0.20	0.30	0.25
L2	0.20	0.30	0.25
L3	—	—	0.40
All Dimensions in mm			

Suggested Pad Layout



Dimensions	Value (in mm)
Z	1.1
G1	0.3
G2	0.2
X	0.7
X1	0.25
Y	0.4
C	0.7

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